

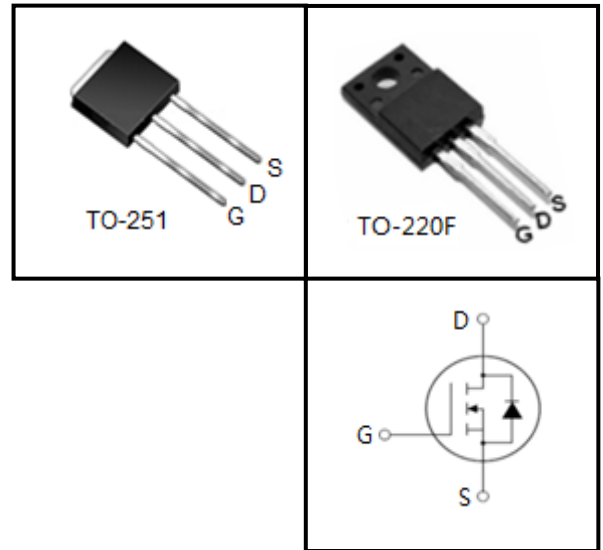
650V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information

Device	Package	Marking
CS3N65LF	TO-220F	CS3N65LF
CS3N65LU	TO-251	CS3N65LU

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value		Unit
		TO-220F	TO-251	
Drain-Source Voltage ($V_{GS} = 0V$)	V_{DSS}	650		V
Continuous Drain Current	I_D	3		A
Pulsed Drain Current (note1)	I_{DM}	12		A
Gate-Source Voltage	V_{GSS}	± 30		V
Single Pulse Avalanche Energy (note2)	E_{AS}	80		mJ
Avalanche Current (note1)	I_{AS}	4		A
Repetitive Avalanche Energy (note1)	E_{AR}	48		mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	30	45	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	$-55 \sim +150$		$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value		Unit
		TO-220F	TO-251	
Thermal Resistance, Junction-to-Case	R_{thJC}	4.1	2.8	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	60	

Specifications $T_J = 25^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	650	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 650V, V _{GS} = 0V, T _J = 25°C	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D = 1.5A	--	3	3.6	Ω
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1.0MHz	--	329	--	pF
Output Capacitance	C _{oss}		--	36	--	
Reverse Transfer Capacitance	C _{rss}		--	4.6	--	
Gate Resistance	R _g	V _{GS} = 0V,V _{DS} = 0V,f = 1.0MHz	--	2.9	--	Ω
Total Gate Charge	Q _g	V _{DD} = 520V, I _D = 3.0A, V _{GS} = 10V	--	12.6	--	nC
Gate-Source Charge	Q _{gs}		--	1.8	--	
Gate-Drain Charge	Q _{gd}		--	6.5	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 325V, I _D = 3.0A, R _G = 25 Ω	--	34	--	ns
Turn-on Rise Time	t _r		--	7.5	--	
Turn-off Delay Time	t _{d(off)}		--	70	--	
Turn-off Fall Time	t _f		--	27	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25 °C	--	--	3	A
Pulsed Diode Forward Current	I _{SM}		--	--	12	
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 1.5A, V _{GS} = 0V	--	--	1.4	V
Reverse Recovery Time	t _{rr}	V _R = 325V,I _S = 3.0A, di _F /dt =100A /μs	--	285	--	ns
Reverse Recovery Charge	Q _{rr}		--	1.42	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 10.0mH, V_{DD} = 70V, R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

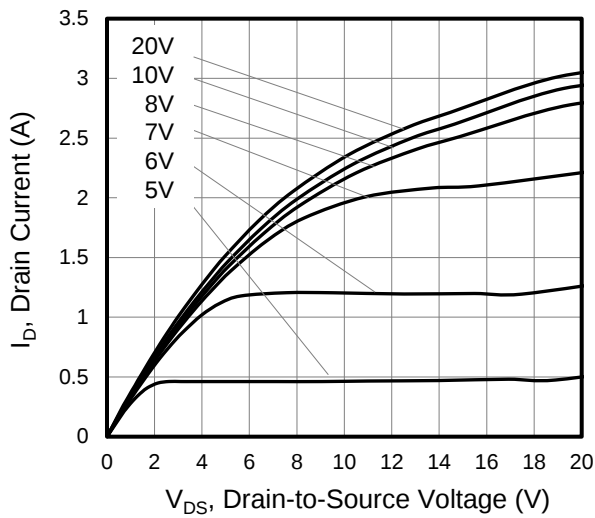


Figure 2. Body Diode Forward Voltage

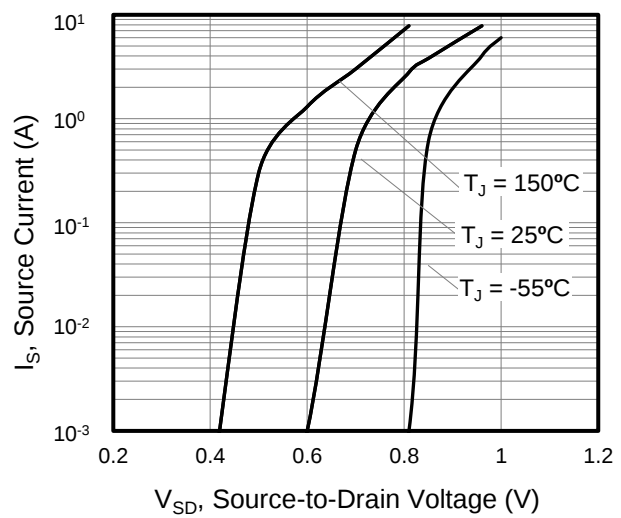
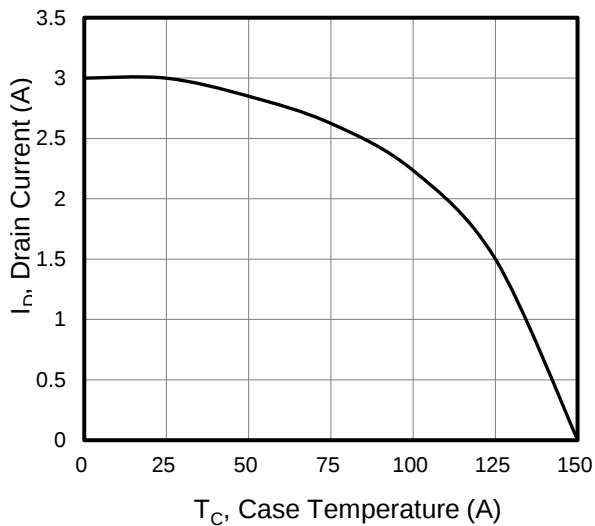


Figure 3. Drain Current vs. Temperature



**Figure 4. Power Dissipation vs. Temperature
TO-252**

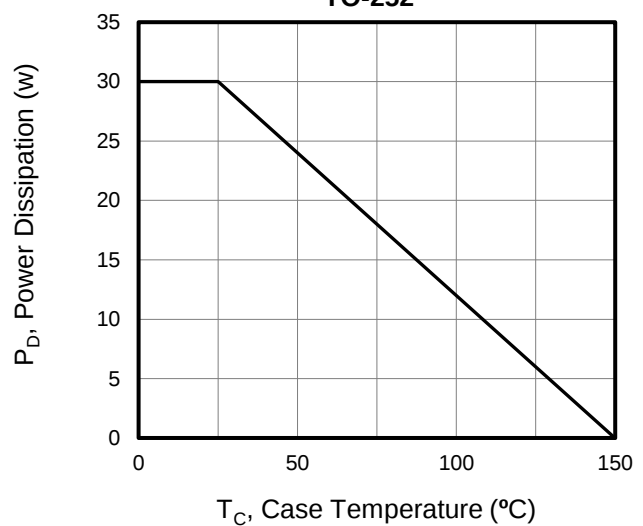


Figure 5. Transfer Characteristics

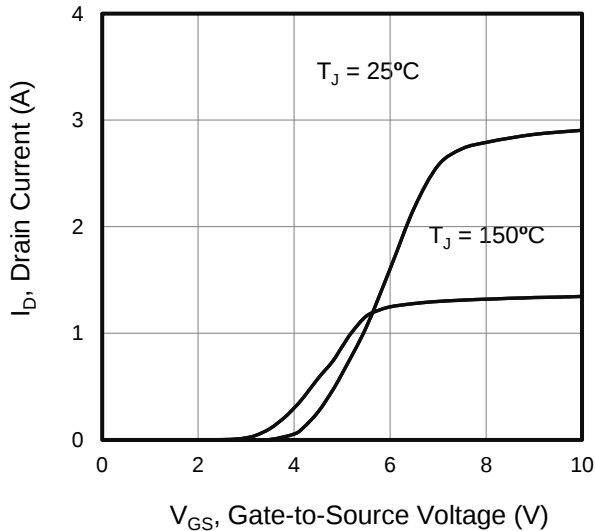
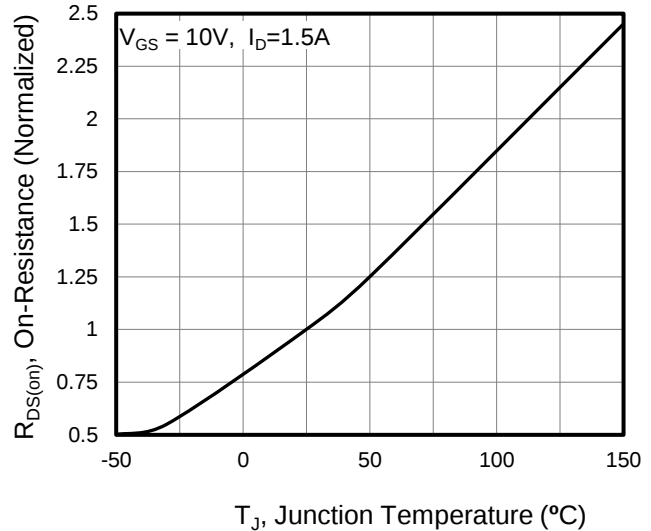


Figure 6. On-Resistance vs. Temperature



Typical Characteristics $T_j = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

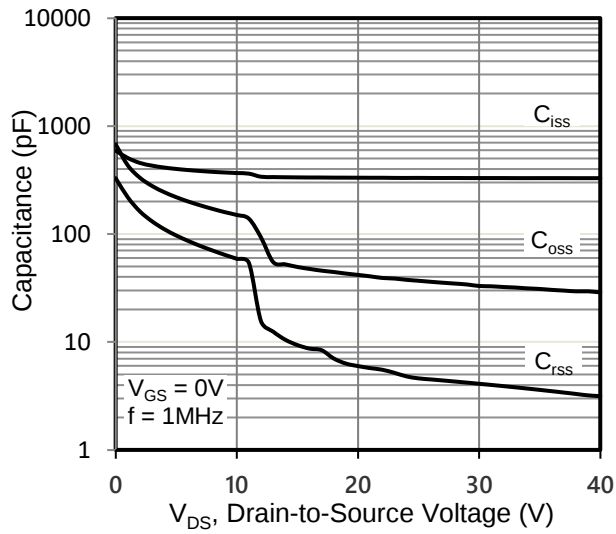


Figure 8. Gate Charge

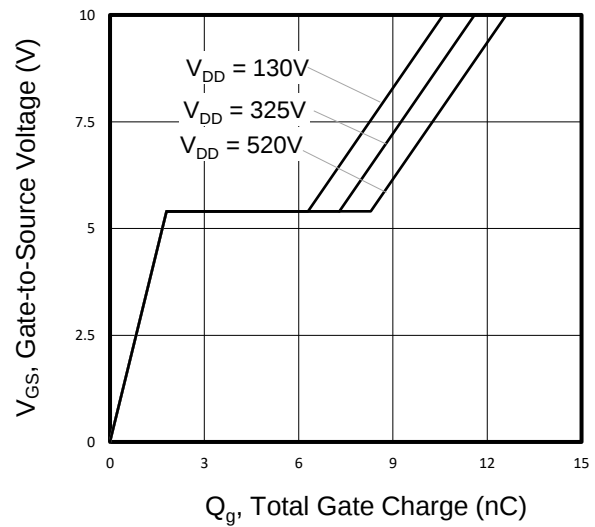


Figure 9. Transient Thermal Impedance TO-220F

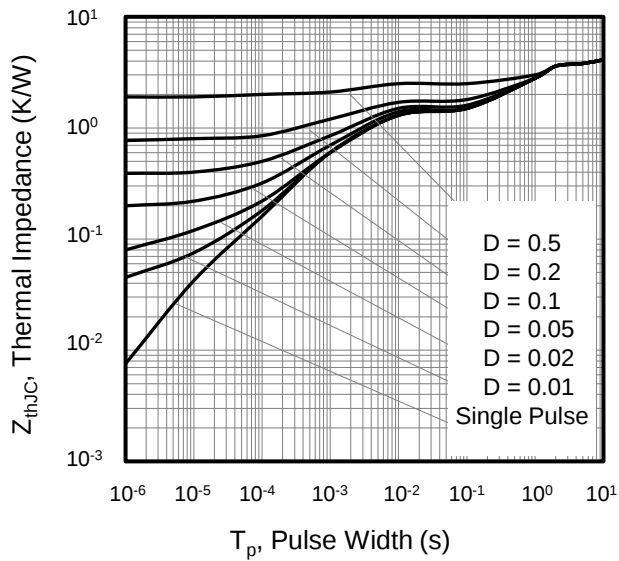


Figure 10. Transient Thermal Impedance TO-251

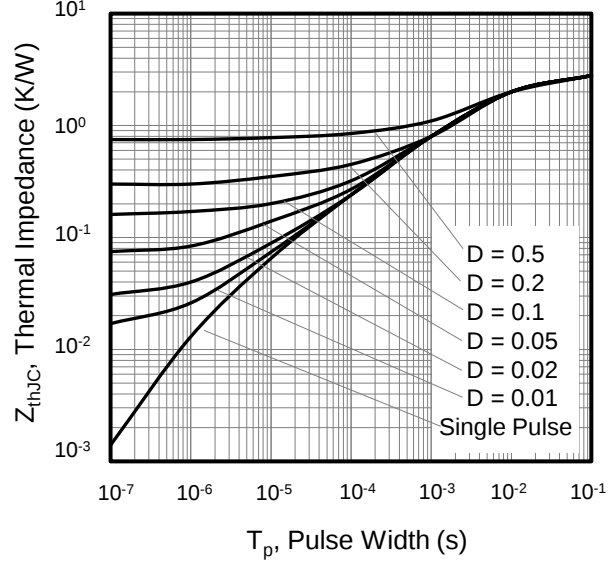
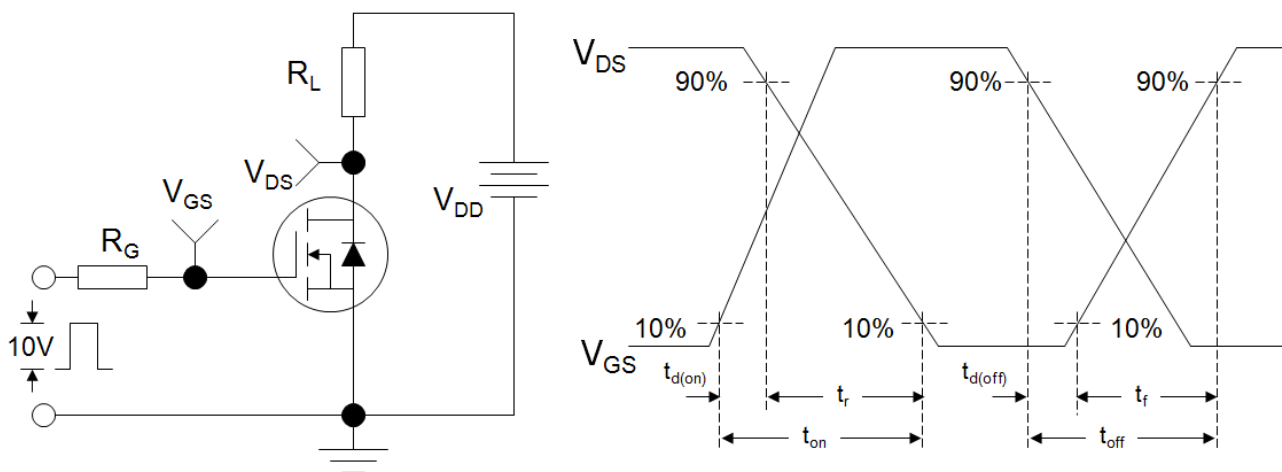


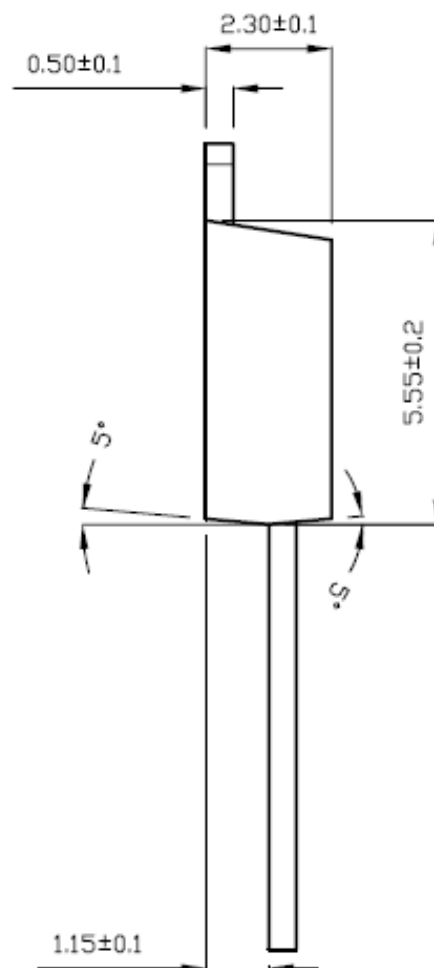
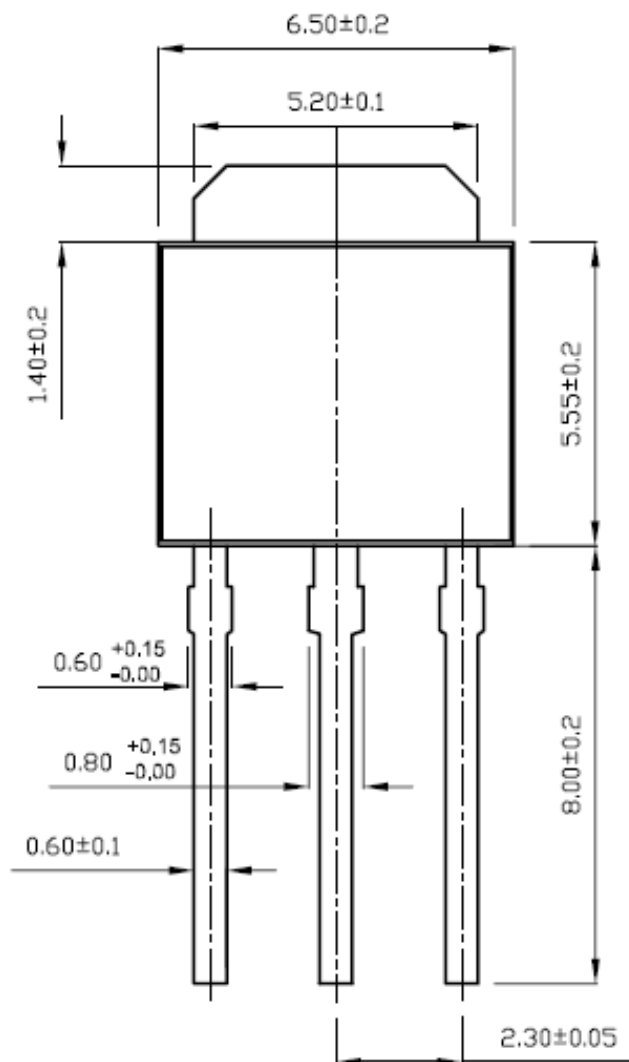
Figure A: Gate Charge Test Circuit and Waveform

Figure B: Resistive Switching Test Circuit and Waveform

Figure C: Unclamped Inductive Switching Test Circuit and Waveform


TO-220F



TO-251



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